

3

SSC80311GS6

P-Channel Enhancement Mode MOSFET

\triangleright Features

V _{DS}	V _{GS}	R _{DS(ON)} Typ.	Ι _D
-30V	±20V	72mΩ@-10V	-2.8A
		106mΩ@-4V5	-2.0A

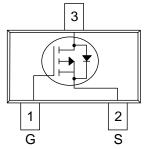
Description \geq

The This device is produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package.

D

Pin configuration

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SOT-23

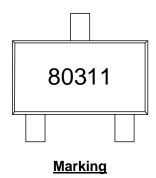
Pin Configuration (Top View)

Applications \geq

- Load Switch
- Portable Devices
- **DCDC** Conversion

Ordering Information \geq

Device	Package	Shipping
SSC80311GS6	SOT-23	3000/Reel







Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain-to-Source Voltage	-30	V
V _{GSS}	Gate-to-Source Voltage	±20	V
ID	Continuous Drain Current ^a	-2.8	А
Ідм	Pulsed Drain Current ^b -11		А
PD	Power Dissipation ^a	1.14	W
TJ	Operation junction temperature	-55~150	°C
T _{STG}	Storage temperature range	-55~150	°C

> Absolute Maximum Ratings ($T_A=25^{\circ}$ unless otherwise noted)

> Thermal Resistance Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Maximum	Unit
Reja	Junction-to-Ambient Thermal Resistance ^a	110	°C/W

Note:

- a. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with T_A=25 °C.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.



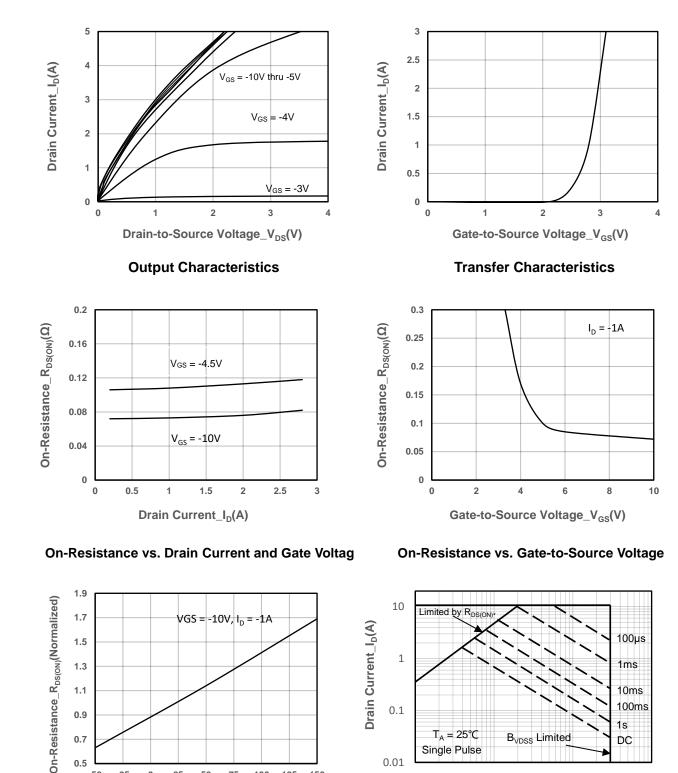


\succ Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	V _(BR) dss	$V_{GS} = 0V, I_D = -250 \mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 uA$	-1	-1.5	-2.5	V
Drain Course On Desistance	RDS(on)	$V_{GS} = -10V, I_D = -2A$		72	90	mΩ
Drain-Source On-Resistance		V _{GS} = -4.5V, I _D = -1A		106	125	
Zero Gate Voltage Drain Current	ldss	V_{DS} = -30V, V_{GS} = 0V			-1	μA
Gate-Source Leak Current	lgss	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			±100	nA
Forward Voltage	V_{SD}	$V_{GS} = 0V$, $I_S = -2A$		-0.84	-1.3	V
Input Capacitance	Ciss			268		pF
Output Capacitance	Coss	$V_{DS} = -15V, V_{GS} = 0V,$		42		
Reverse Transfer Capacitance	Crss	f = 1MHz		34		
Turn-on Delay Time	T _{D(ON)}			7.1		ns
Rise Time	Tr	$V_{DS} = -30V, I_D = -1A, R_L$ = $6\Omega, V_{GS} = -10V, R_G = -3\Omega$		20		
Turn-off Delay Time	T _{D(OFF)}			35		
Fall Time	T _f			11		
Total Gate Charge	Q _G	- V _{DS} = -30V, V _{GS} = -10V,		11		nC
Gate to Source Charge	Q _{GS}			2.2		
Gate to Drain Charge	Q _{GD}	- I _D = -1A		2.5		



Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



On-Resistance vs. Junction Temperature

50

Gate-to-Source Voltage_V_{GS}(V)

75

100 125 150

Safe Operating Area vs. Junction-to-Ambient

 $\label{eq:V_DS} \begin{array}{l} $ Drain-to-Source \ Voltage_V_{DS}(V) $ *V_{GS}>mininum \ V_{GS} \ at \ which \ R_{DS(ON)} \ is \ specified \\ \end{array}$

1

B_{VDSS} Limited

10

100

10ms

100ms

1s

DC

0.1

0.01

0.1

T_A = 25°C

Single Pulse

1.1

0.9

0.7

0.5 -50

-25

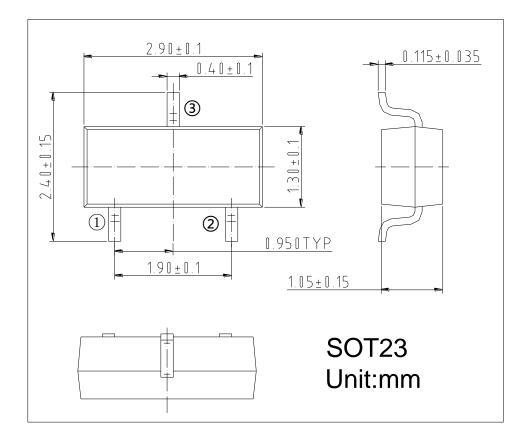
0

25

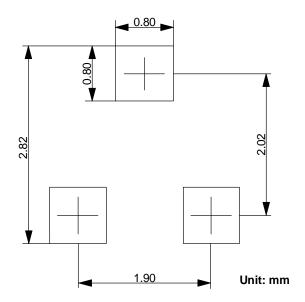




Package Information



Suggested Pad Layout





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